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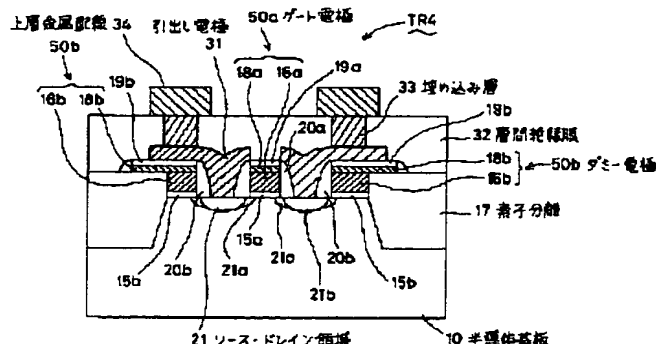
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APPLICANT : MATSUSHITA ELECTRIC IND CO LTD;

INVENTOR : FUJII MINORU;

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TITLE : SEMICONDUCTOR DEVICE AND ITS
MANUFACTURE



ABSTRACT : PURPOSE: To provide a semiconductor device which has little dispersion in processing dimension dependent upon the difference of gate patterns and is high in the degree of integration and operation speed, and further provide its manufacturing method.

CONSTITUTION: This semiconductor device is equipped with an element isolating region 17 projecting from a semiconductor substrate 10 in an active region, a gate electrode 50a made within the active region, and a pair of dummy electrodes 50b made on the region straddling the active region and the element isolating region 17 and extended in roughly parallel with the gate electrode 50a. The gate electrode 50a and the dummy electrode 50b are constituted of lower films 16a and 16b and upper films 18a and 18b, respectively. The lower film 18b of the dummy electrode 50b is made on a level with the element isolating region 17, and besides in contact with the side flank of the element isolating region 17. Since all gate electrodes 50a can be made within a line and space pattern by the dummy electrode 50b, the dimension after finish of processing of the gate electrodes 50a can be made equal, and the micronization of gate length becomes possible.

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